

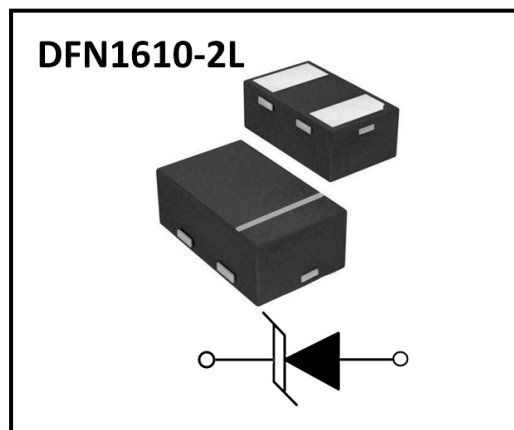
BN5A241V

ESD Protection Diode

Features

- 1260Watts peak pulse power ($t_p = 8/20\mu s$)
- Unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping Voltage
- Low leakage current
- Protection one data/power line
- IEC 61000-4-2 $\pm 30kV$ contact ; $\pm 30kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 30A (8/20 μs)

Package



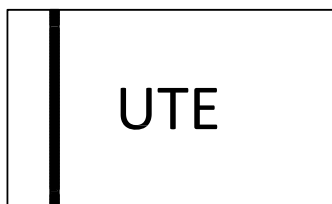
Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

Mechanical Characteristics

- DFN1610-2L package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Marking



Ordering information

Order code	Package	Base qty	Delivery mode
BN5A241V	DFN1610-2L	10k	Tape and reel

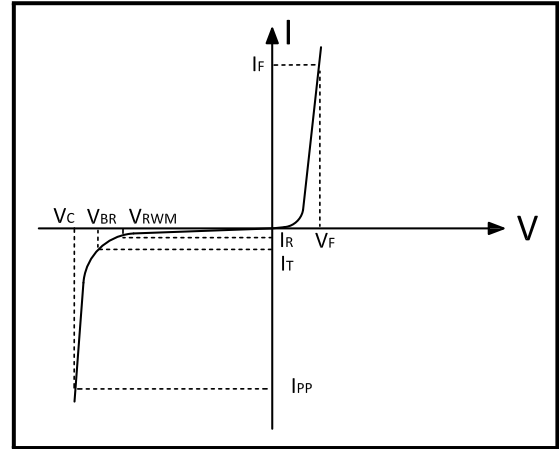


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ESD Protection Diode

Electrical Parameters ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Note: 8/20us pulse Waveform.

Absolute Maximum Rating

Rating	Symer	Value	Units
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	P_{PP}	1260	Watts
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I_{PP}	30	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	30	KV
ESD per IEC 61000-4-2 (Contact)		30	
Lead Soldering Temperature	T_L	260(10seconds)	$^\circ\text{C}$
Junction Temperature	T_J	-55 to + 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to + 150	$^\circ\text{C}$

Electrical Characteristics

Parameter	Symer	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}	—	—	—	24.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	26.7	27.5	30.0	V
Reverse Leakage Current	I_R	$V_{RWM} = 24\text{V}, T = 25^\circ\text{C}$	—	0.1	0.5	μA
Peak Pulse Current	I_{PP}	$t_p = 8/20\mu\text{s}$	—	—	30	A
Clamping Voltage	V_C	$I_{PP} = 30\text{A}, t_p = 8/20\mu\text{s}$	—	40	42	V
Junction Capacitance	C_j	$V_R = 0\text{V}, T = 25^\circ\text{C}, f = 1\text{MHz}$	—	200	250	pF



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

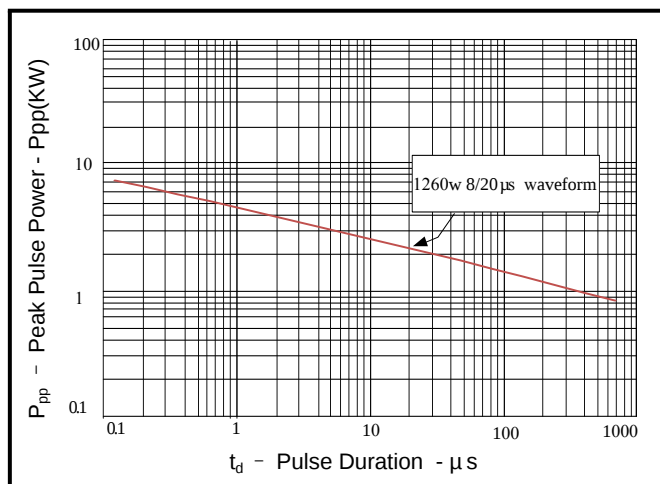


Figure 2: Power Derating Curve

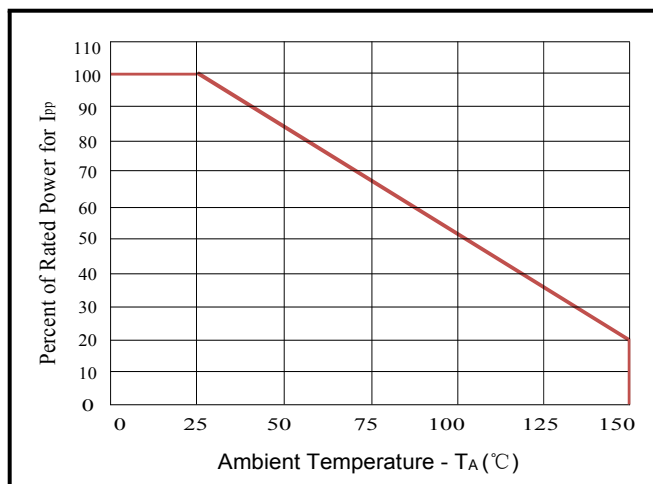


Figure 3: Pulse Waveform

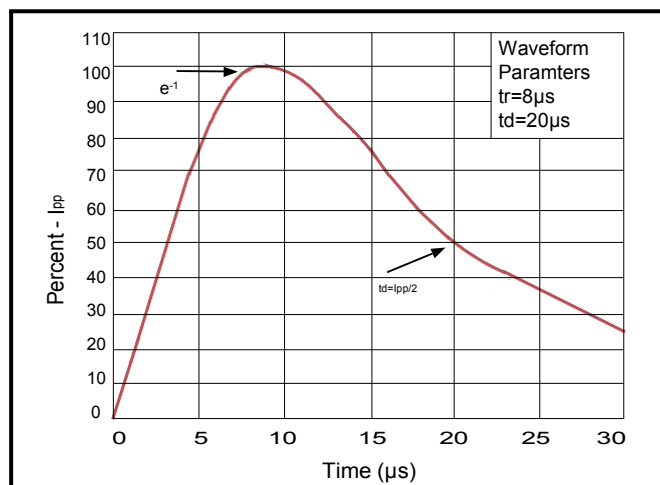
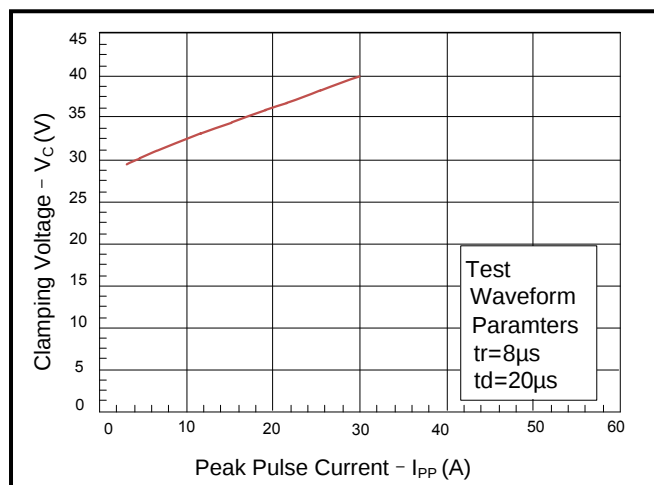


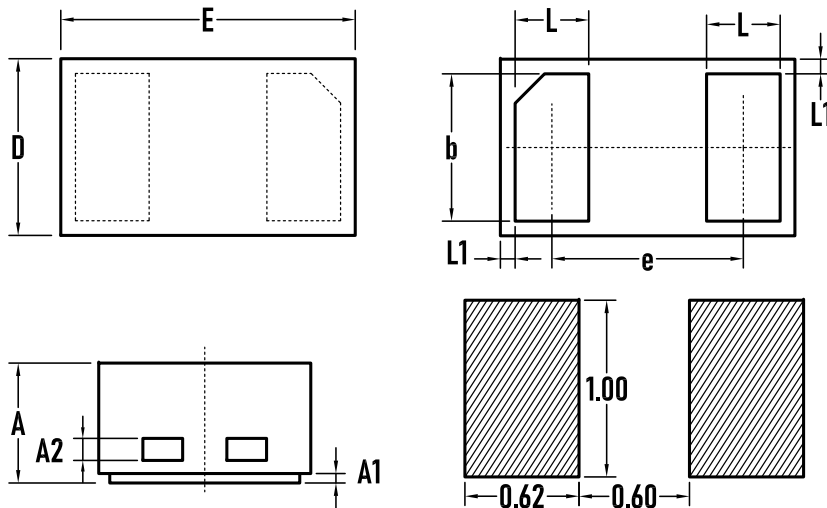
Figure 4: Clamping Voltage vs. Ipp



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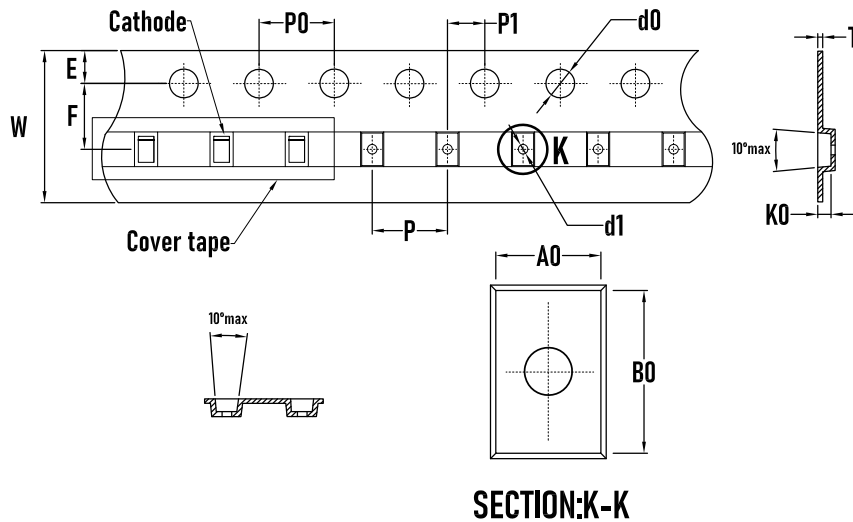
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Outline Drawing – DFN1610-2L



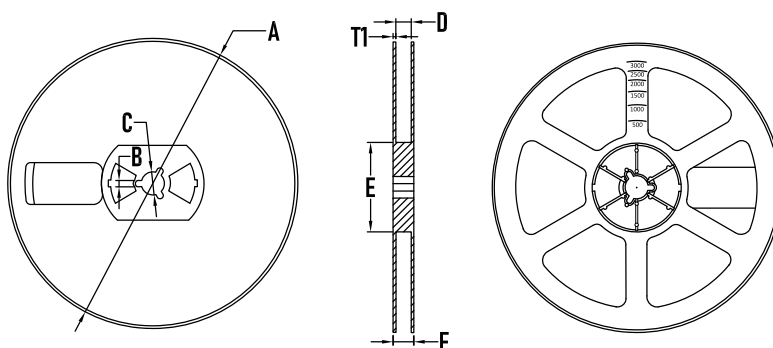
SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	0.45	0.50	0.55
A1	—	0.02	0.05
A2	0.119	0.127	0.135
E	1.55	1.60	1.65
D	0.95	1.00	1.05
b	—	0.80	—
e	1.1039BSC		
L	0.35	0.40	0.45
L1	0.05REF		

Packaging Tape - DFN1610



SYMBOL	MILLIMETER
A0	1.11±0.05
B0	1.72±0.05
d0	1.5 ^{+0.1} ₋₀
d1	0.50±0.1
E	1.75±0.10
F	3.50±0.05
K0	0.68±0.05
P	4.00±0.1
P0	4.00±0.10
P1	2.00±0.05
W	8.00 ^{+0.03} _{-0.01}
T	0.25±0.05

Packaging Reel



SYMBOL	MILLIMETER
A	178±1
B	3.5±0.2
C	14.3±0.2
D	9.8 ⁺² ₋₁
E	54.5±0.5
F	12.4±0.5
T1	1.0±0.2
Quantity	3000PCS

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Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

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